

ABSTRACT OF THE DISCLOSURE

In a MOS type sensor including a floating diffusion (FD) amplifier in each pixel, the number of pulse lines is reduced, so as to improve the numerical aperture. For this purpose, a read pulse for a read transistor of a first pixel and a reset pulse for a reset transistor of a second pixel adjacent to the first pixel in a column direction are supplied through a common gate line; a LOW level potential of a drain line connected to a drain region (a region for supplying a pulse voltage to an FD portion through the reset transistor) of the first pixel is set to a potential higher than a potential depth of a photodiode of the first pixel in resetting the second pixel; and potential below the gate of the reset transistor of the first pixel obtained by applying a LOW level voltage to this gate is set to a potential higher than the LOW level potential of the drain line.